

Fig.1A  
Related Art

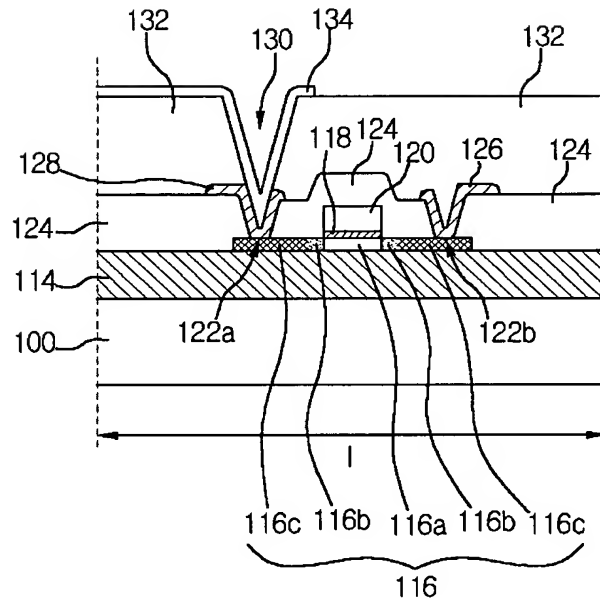


Fig.1B  
Related Art

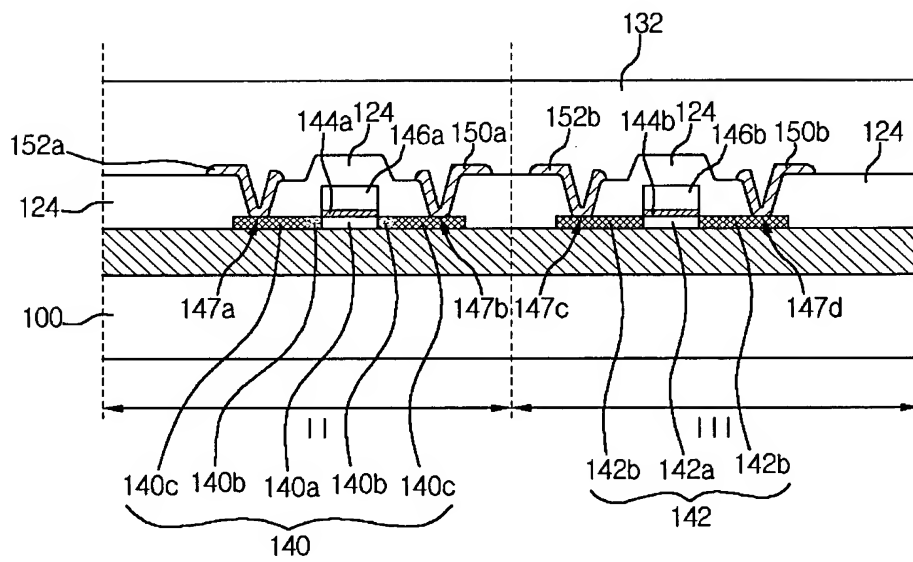
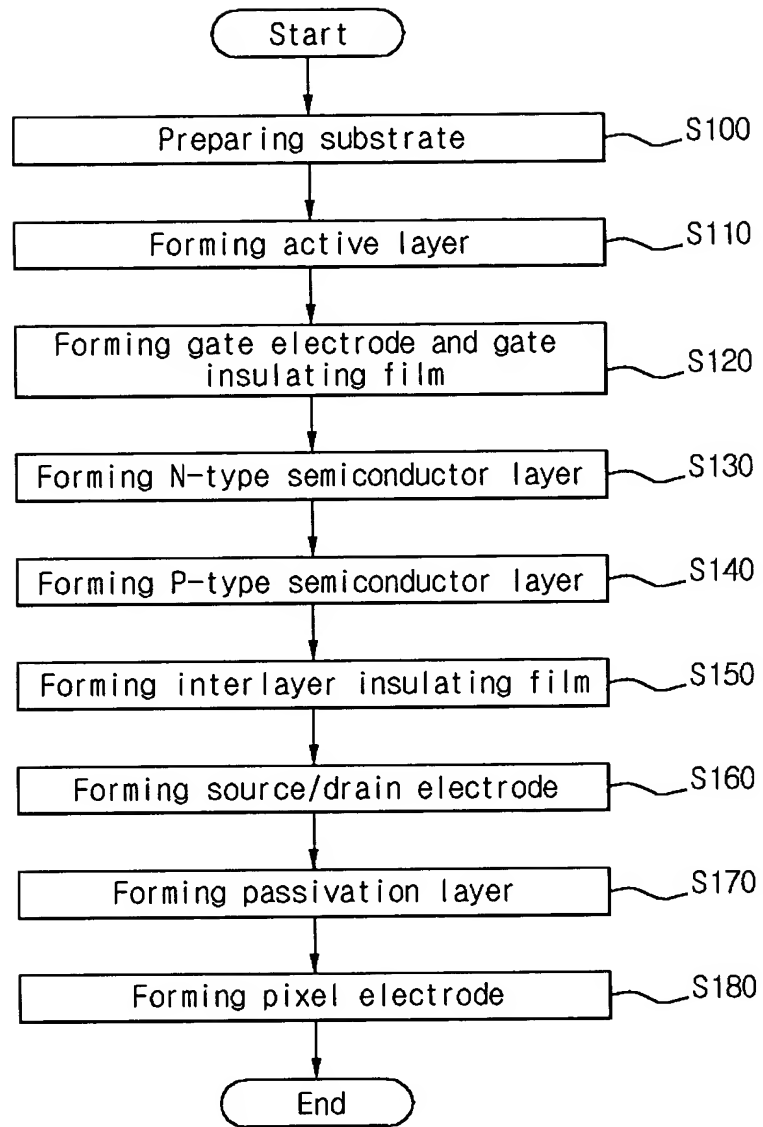


Fig.2  
Related Art



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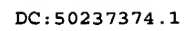


Fig. 10 is a cross-sectional view of a semiconductor device. It shows a substrate 200 with a layer 214 on top. A central structure 218 is surrounded by a layer 220. A layer 224 is on top of 220. A group of five curved lines, labeled 216a, 216b, 216b, 216b, and 216c, are shown below 214, with a bracket 216 underneath them. A vertical dashed line is on the left, and a horizontal line labeled IV is on the right.

Fig. 10 is a cross-sectional view of a semiconductor device. The device includes a substrate 200 with a layer 214. A gate structure 218 is formed on a gate dielectric 220. The gate structure is surrounded by a layer 224. Side gates 222a and 222b are formed on the side surfaces of the gate structure. The side gates are connected to a common terminal 216 via contacts 216a, 216b, and 216c. A label IV is present on the right side.

This cross-sectional view shows a central gate structure 218 on a gate dielectric 214. The gate structure is flanked by source/drain regions 222a and 222b. A central channel region 220 is located between the source/drain regions. The device is formed on a substrate 200. A dashed line 228 indicates a cross-section through the device. The top surface is covered by a layer 232. The gate structure is formed by a layer 230 and a top layer 234. The source/drain regions are formed by a layer 226. The channel region is formed by a layer 229. The substrate 200 is divided into two regions, 216a and 216b, by a vertical line 216c. The regions 216a and 216b are labeled as 216.

Fig.5

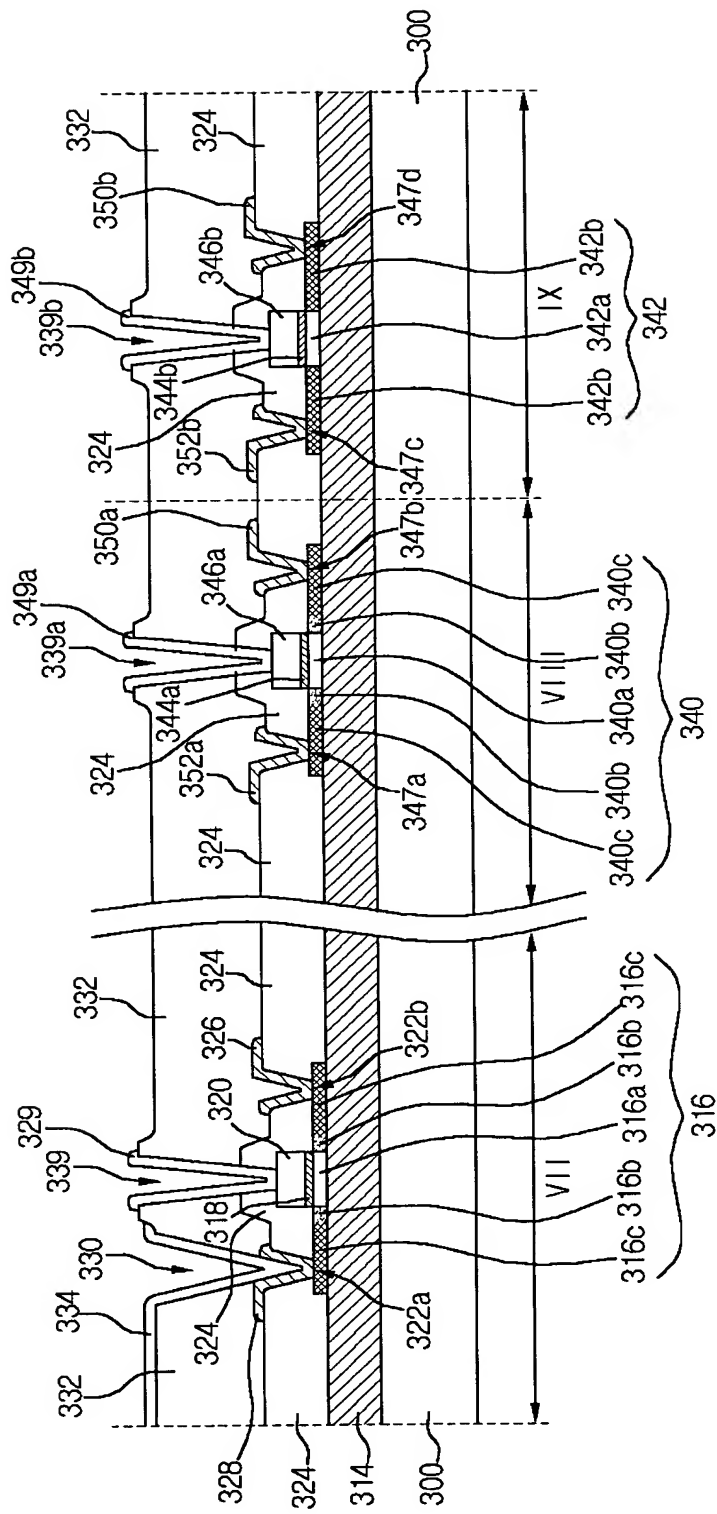


Fig.6A

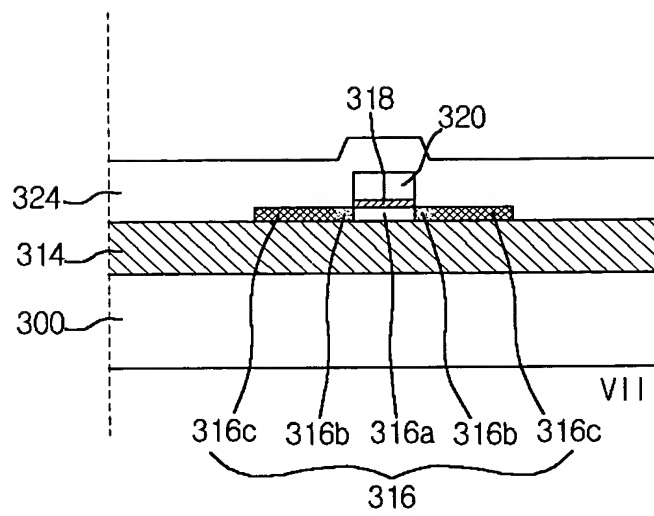


Fig.6B

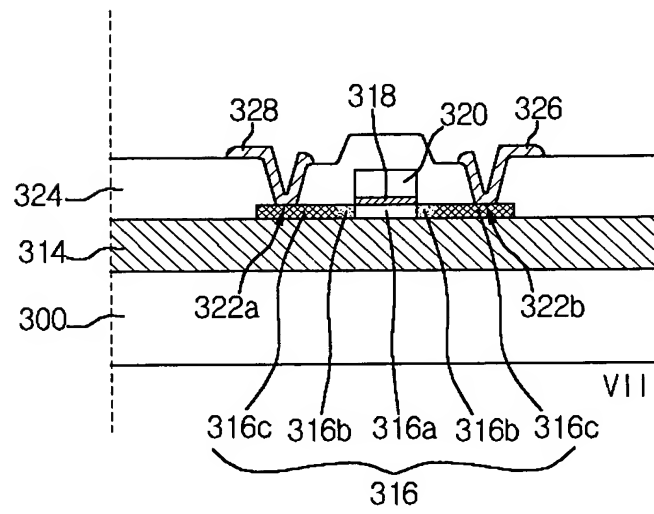


Fig.6C

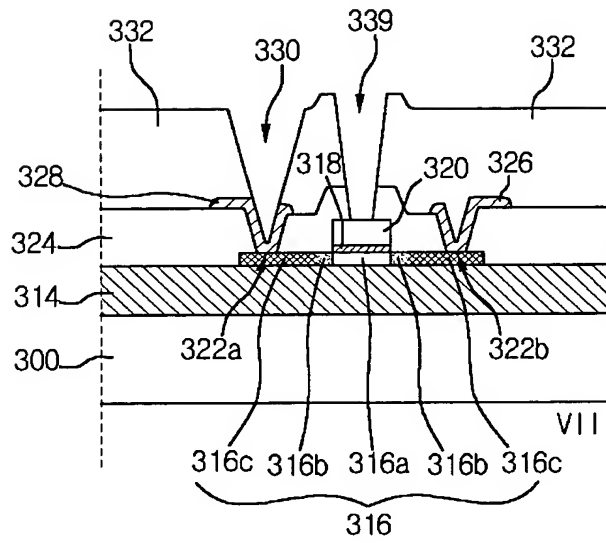


Fig.6D

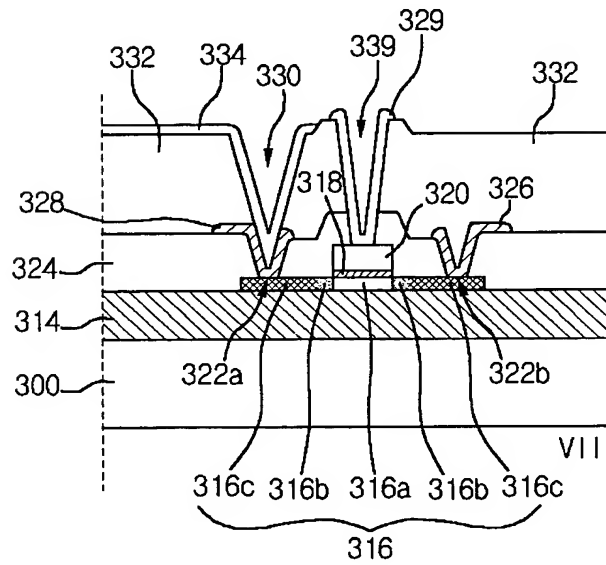




Fig.7

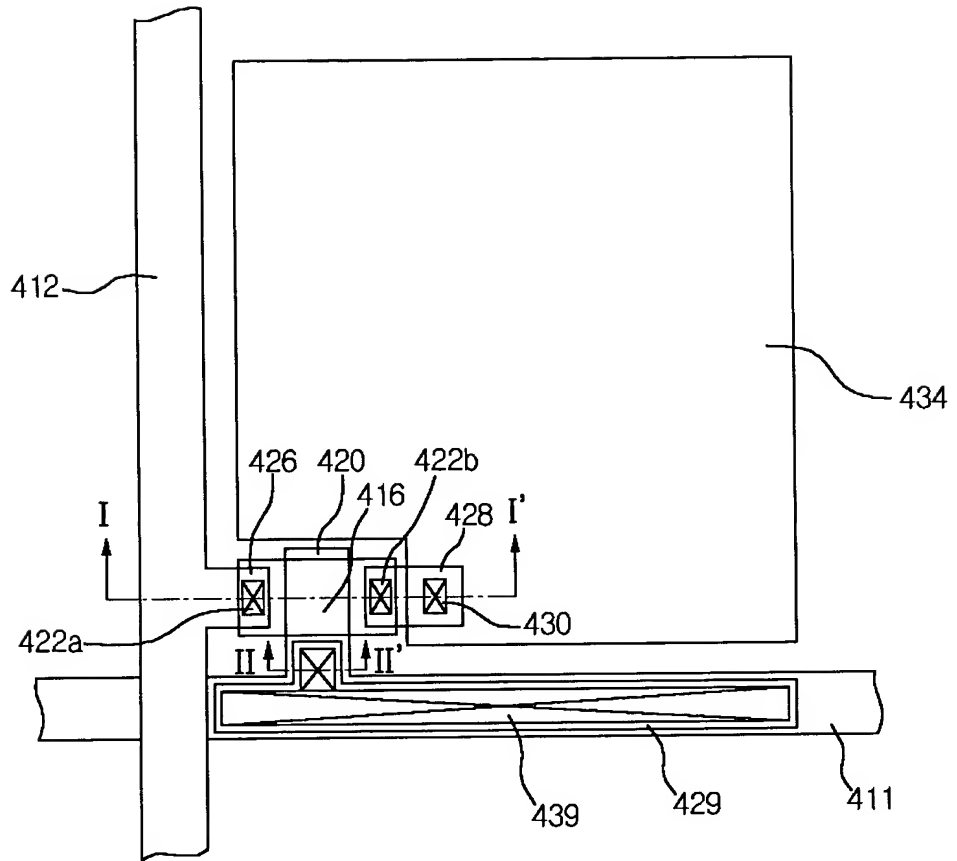


Fig.8A

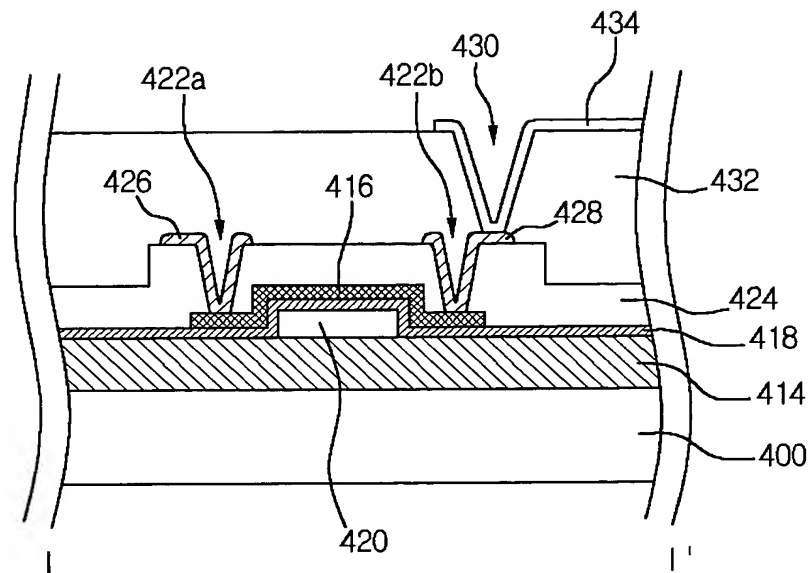


Fig.8B

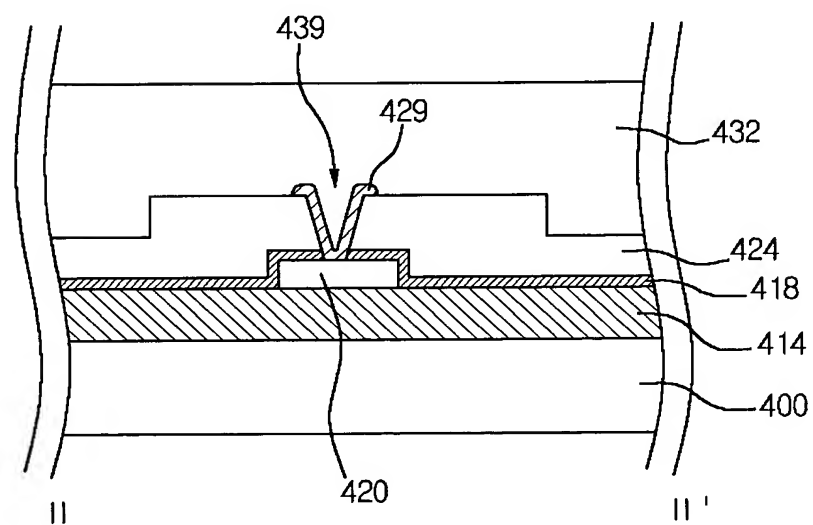


Fig.9

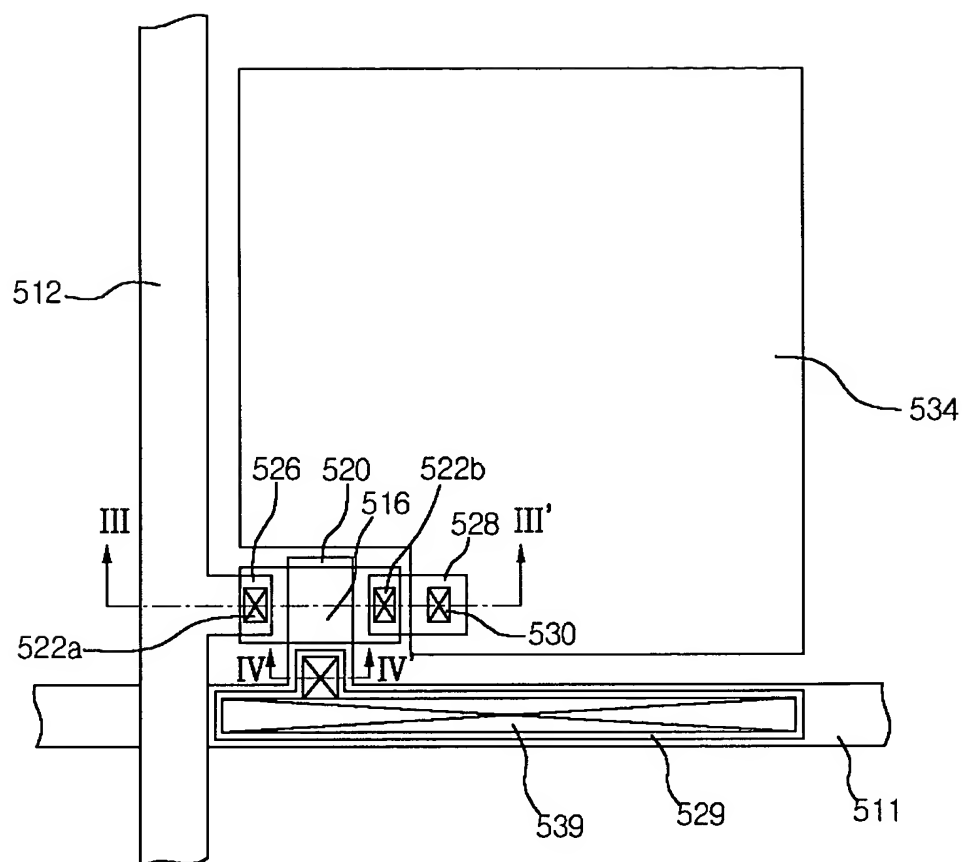


Fig.10A

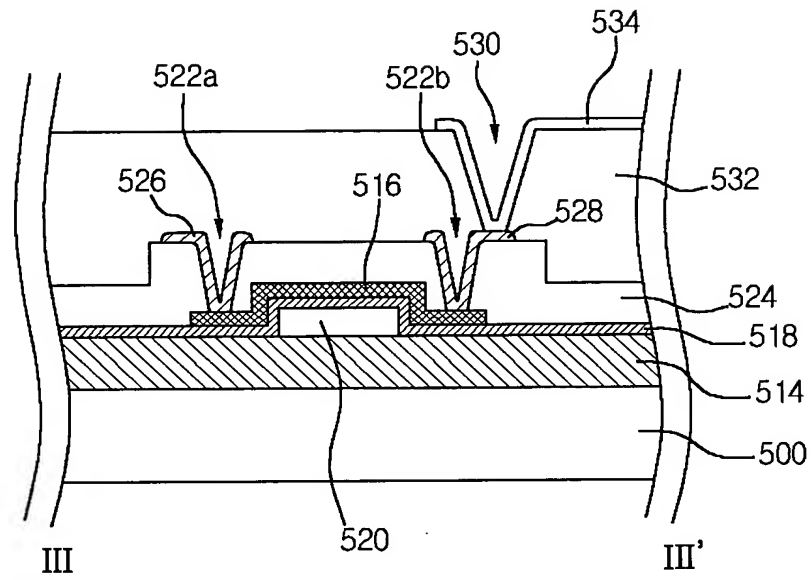


Fig.10B

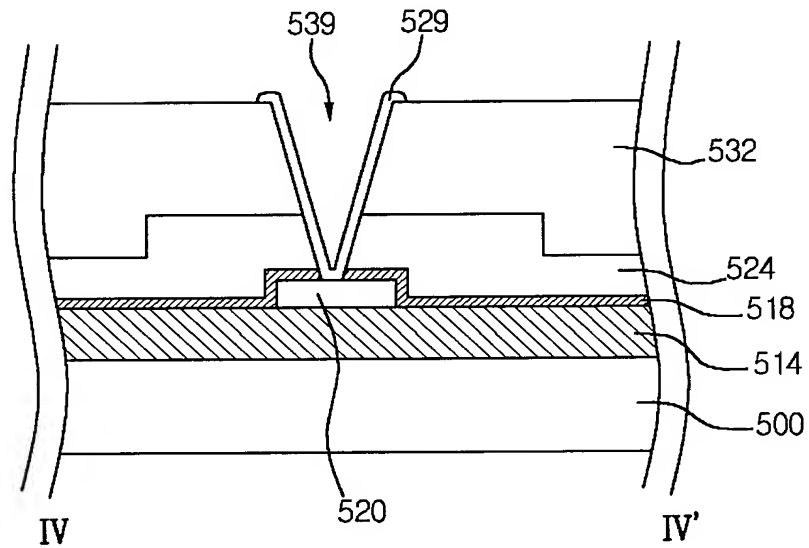


Fig.11A

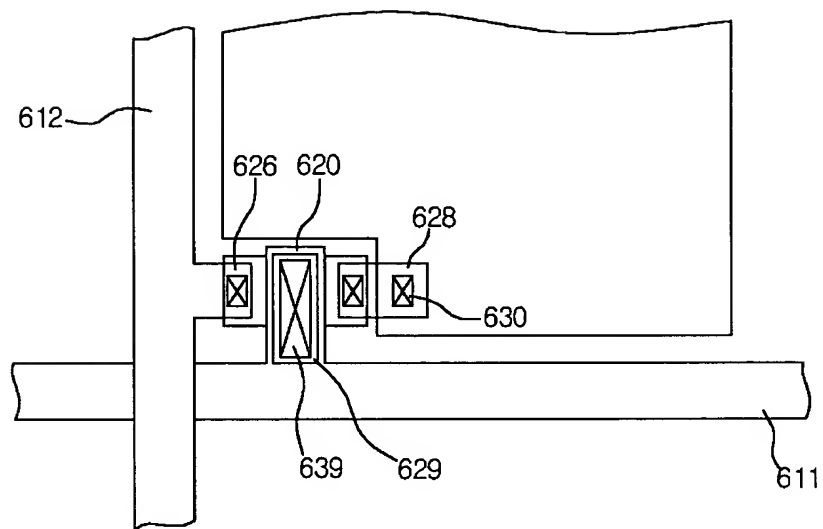


Fig.11B

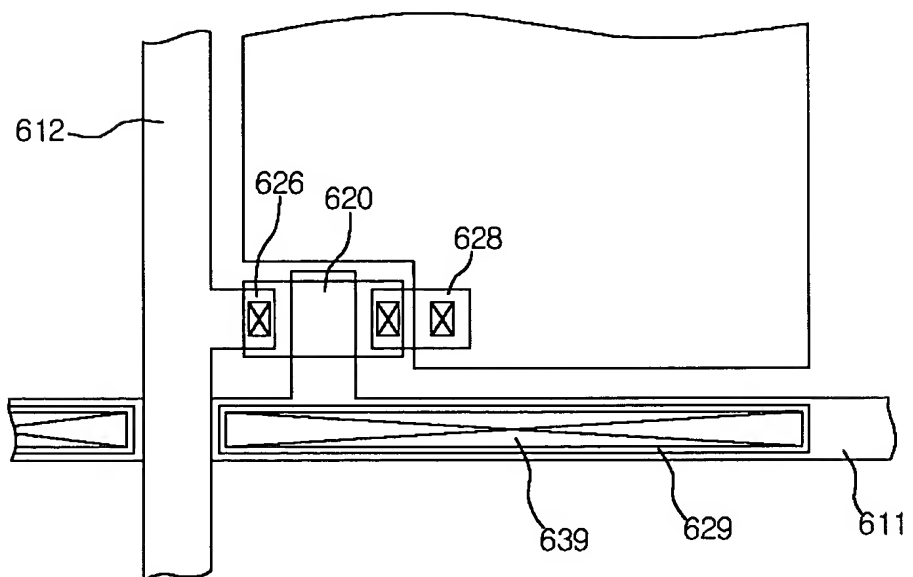


Fig.11C

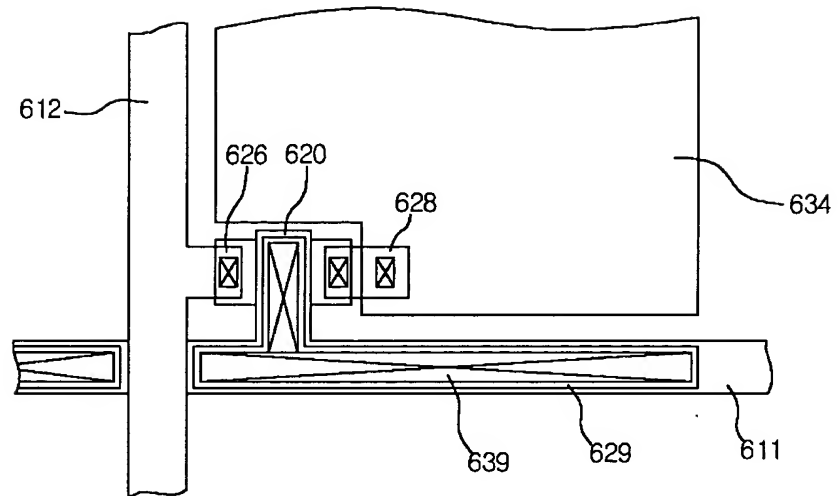


Fig.11D

